

Superharmonic Injection Locked Oscillators as Low Power Frequency Dividers

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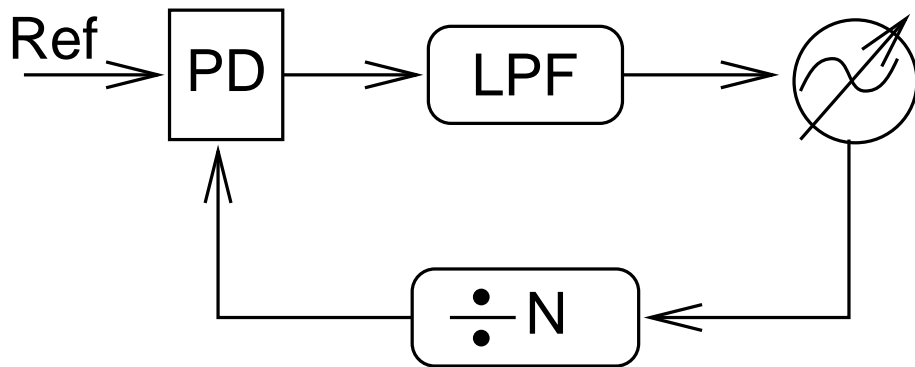
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OUTLINE:

- Frequency dividers
 - Applications
 - Power and frequency issues (limitations/relations)
- Injection locked oscillators
 - Review of definitions
 - Mathematical model
 - Application as injection locked frequency dividers
- Simulation and measurement results
- Conclusion

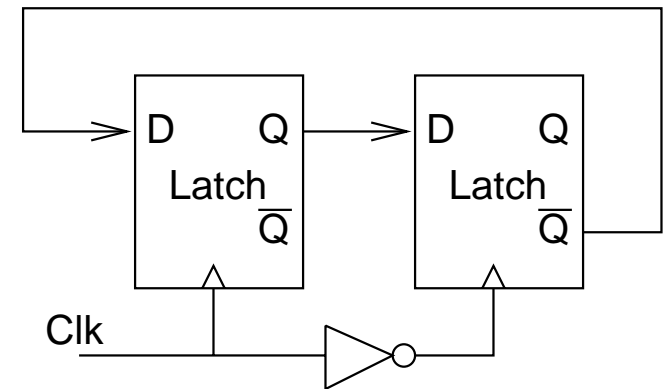
FREQUENCY DIVIDERS

- Frequency dividers are widely used in the feedback path of phase locked loops.



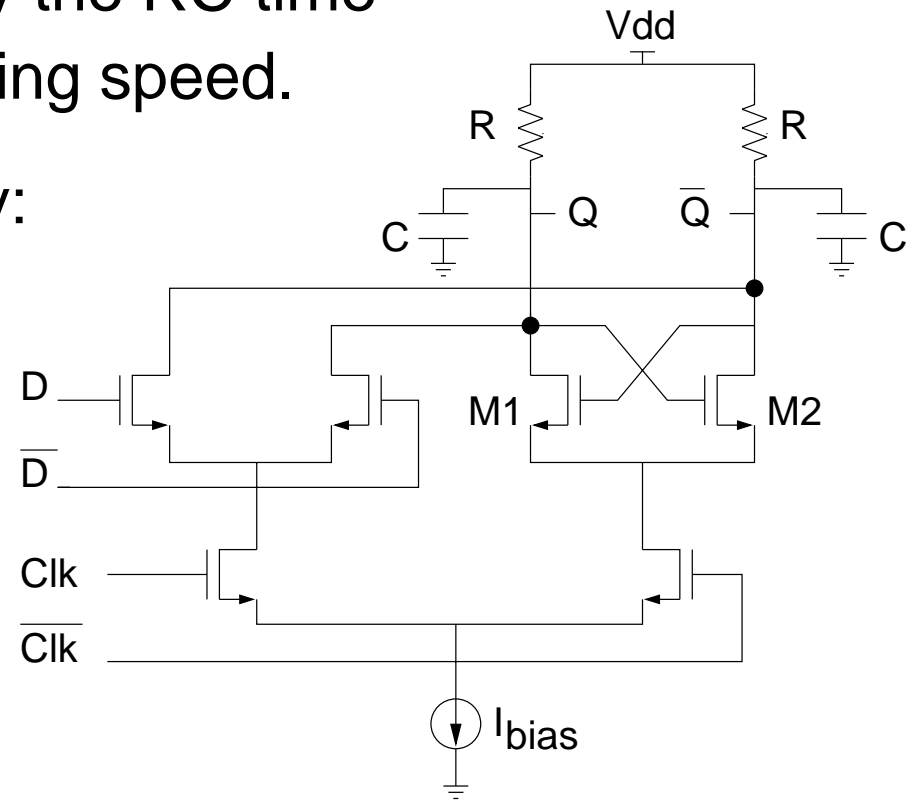
- Conventional frequency dividers:

- Flip-flops are used to divide frequency.
- Flip-flop based dividers are wide band.
- Power consumption increases with the frequency of operation.



CONVENTIONAL FREQUENCY DIVIDERS

- Maximum frequency is limited by the RC time constant as well as M1/M2 latching speed.
- To operate at a higher frequency:
 - Reduce $R \Rightarrow$
 - * Reduce RC time constant.
 - * Increase M1/M2 latch time.
 - Increase $I_{bias} \Rightarrow$
 - * M1 and M2 can latch.
 - * Enough swing.
 - Increase power consumption.
- In CMOS logics, dynamic power $\propto CV^2f$.



SOLUTION

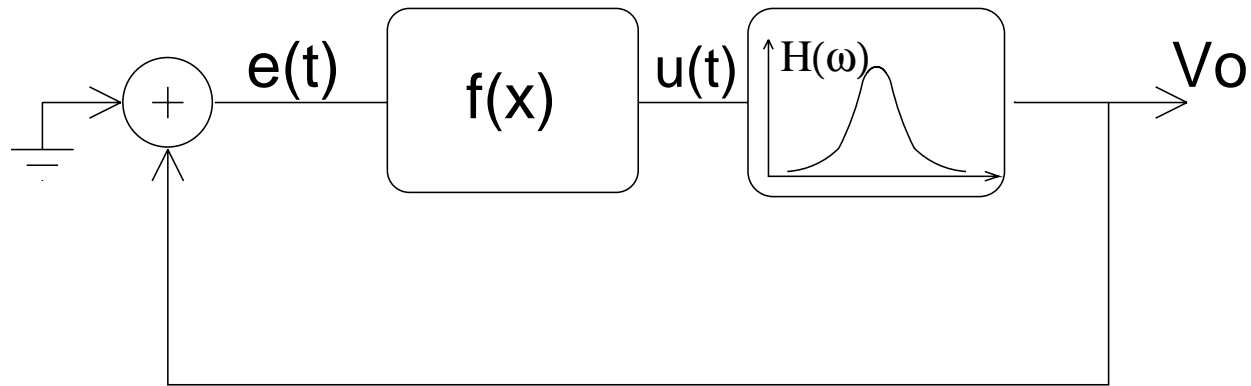
- Observation: Most wireless systems are narrow band.
- In order to increase speed and reduce power consumptions of frequency dividers:

Use resonators to trade off bandwidth for power and maximum frequency of operation.

INJECTION LOCKED OSCILLATORS

- By impressing an oscillator with an external (incident) signal, frequency locking can be achieved.
 - First-harmonic injection locked oscillators ($f_i = f_o$).
 - Subharmonic injection locked oscillators ($f_i = \frac{1}{N} f_o$).
 - Superharmonic injection locked oscillators ($f_i = N \times f_o$).

MODEL FOR LC OSCILLATORS



$f(x)$: A nonlinear function.

$$H(\omega) = \frac{H_0}{1 + j2Q\frac{\Delta\omega}{\omega_r}}$$

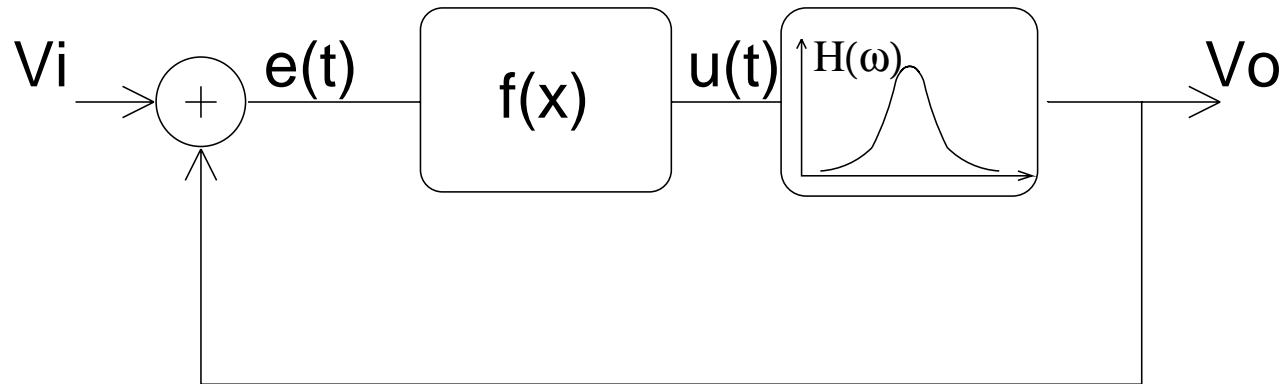
- Oscillation condition:

- loop gain of unity

- * Gain condition: $|gain|=1$

- * Phase condition: $\Delta\varphi = 0$

MODEL FOR INJECTION LOCKED LC OSCILLATORS



$$v_o(t) = V_o \cos(\omega_o t)$$

$$v_i(t) = V_i \cos(\omega_i t + \phi)$$

$$u(t) = f[e(t)] = f[v_o(t) + v_i(t)]$$

- Oscillation condition should be satisfied in the presence of the incident signal.

MATHEMATICAL MODEL (FUNDAMENTAL EQUATIONS)

- Satisfying the oscillation conditions \Rightarrow

$$V_o = H_o \left[K_{0,1} + \frac{1}{2} \sum_{m=1}^{\infty} K_{m,Nm\pm 1} \cos(m\phi) \right]$$

$$2V_o Q \frac{\Delta\omega}{\omega_r} = \frac{H_o}{2} \sum_{m=1}^{\infty} K_{m,Nm\pm 1} \sin(m\phi)$$

SPECIAL CASE (DIVIDE BY TWO)

$$f(x) = a_0 + a_1x + a_2x^2 + a_3x^3$$

- Phase condition:

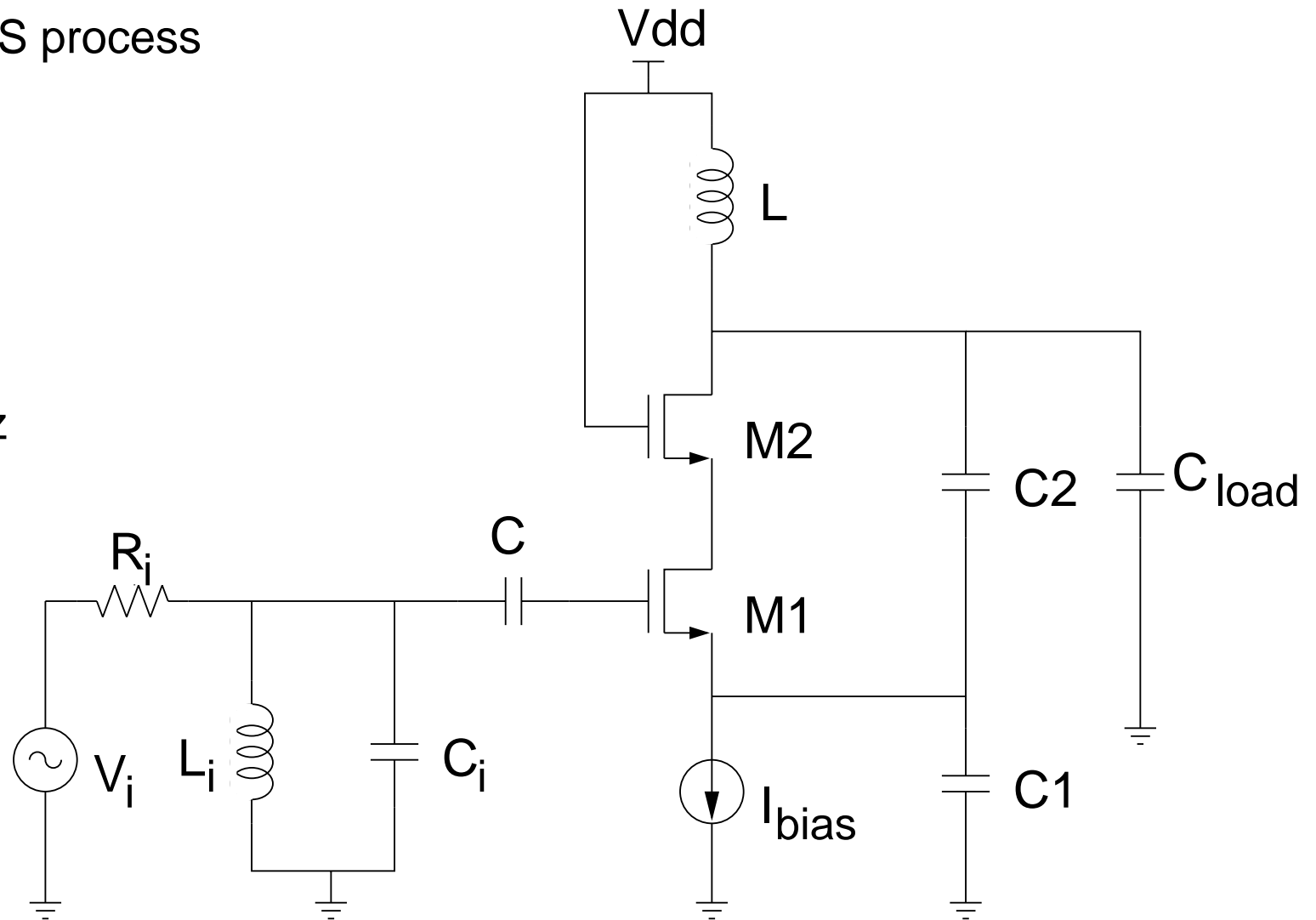
$$\left| \frac{\Delta\omega}{\omega_r} \right| < \left| \frac{H_0 a_2 V_i}{2Q} \right|, \quad \frac{H_0}{Q} = \frac{LQ\omega_r}{Q} = L\omega_r$$

- Gain condition:

$$V_o = \sqrt{\frac{4}{3} \frac{1}{a_3 H_0} \left[1 - H_0 \left(a_1 + \frac{3}{2} a_3 V_i^2 + a_2 V_i \cos(\phi) \right) \right]}$$

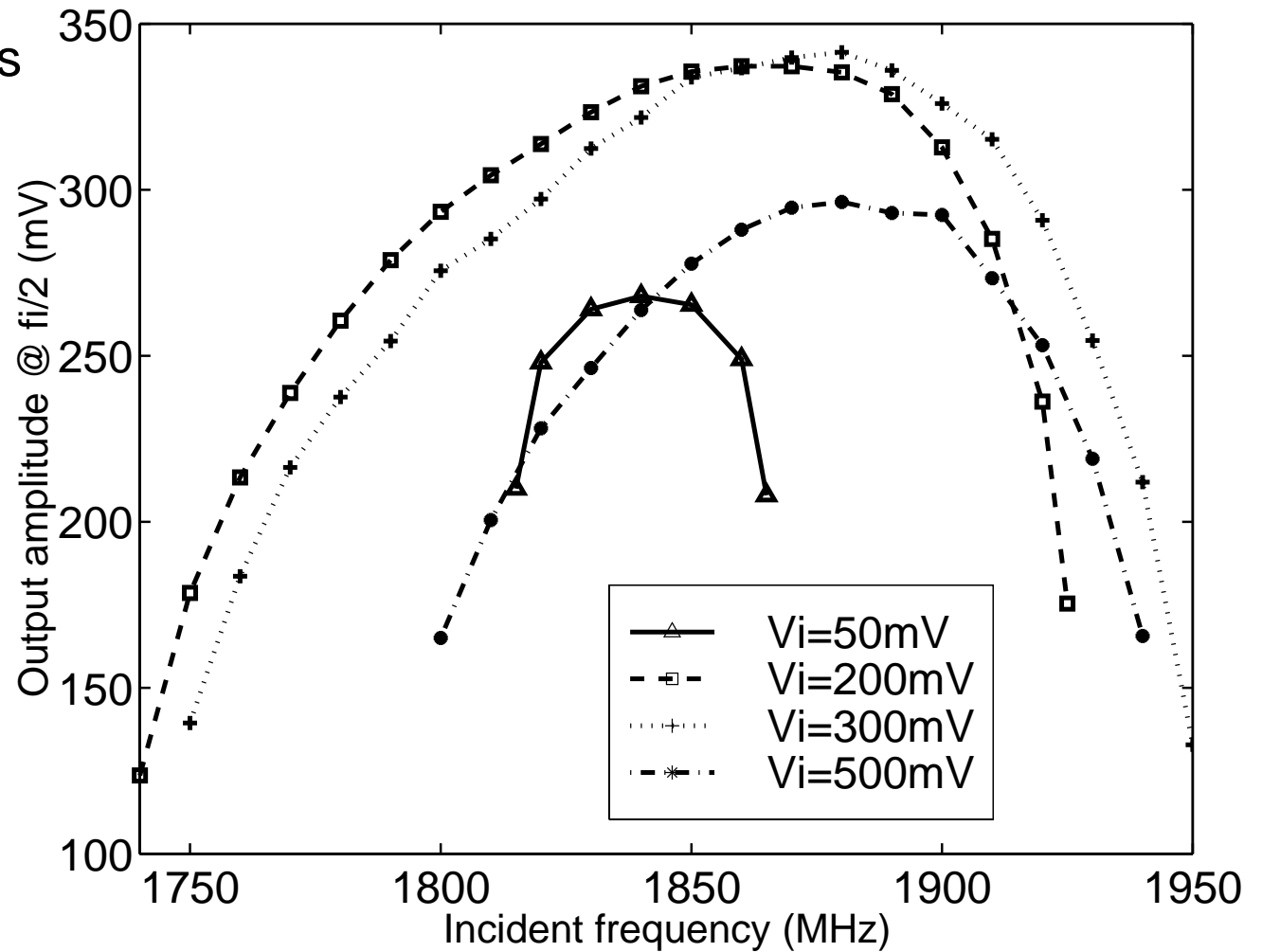
SINGLE ENDED ILFD

- $0.5\mu\text{m}$ CMOS process
- $V_{\text{dd}}=2.5\text{V}$
- $I_{\text{bias}}=1.2\text{mA}$
- $f_o=920\text{MHz}$
- $f_i=1840\text{MHz}$



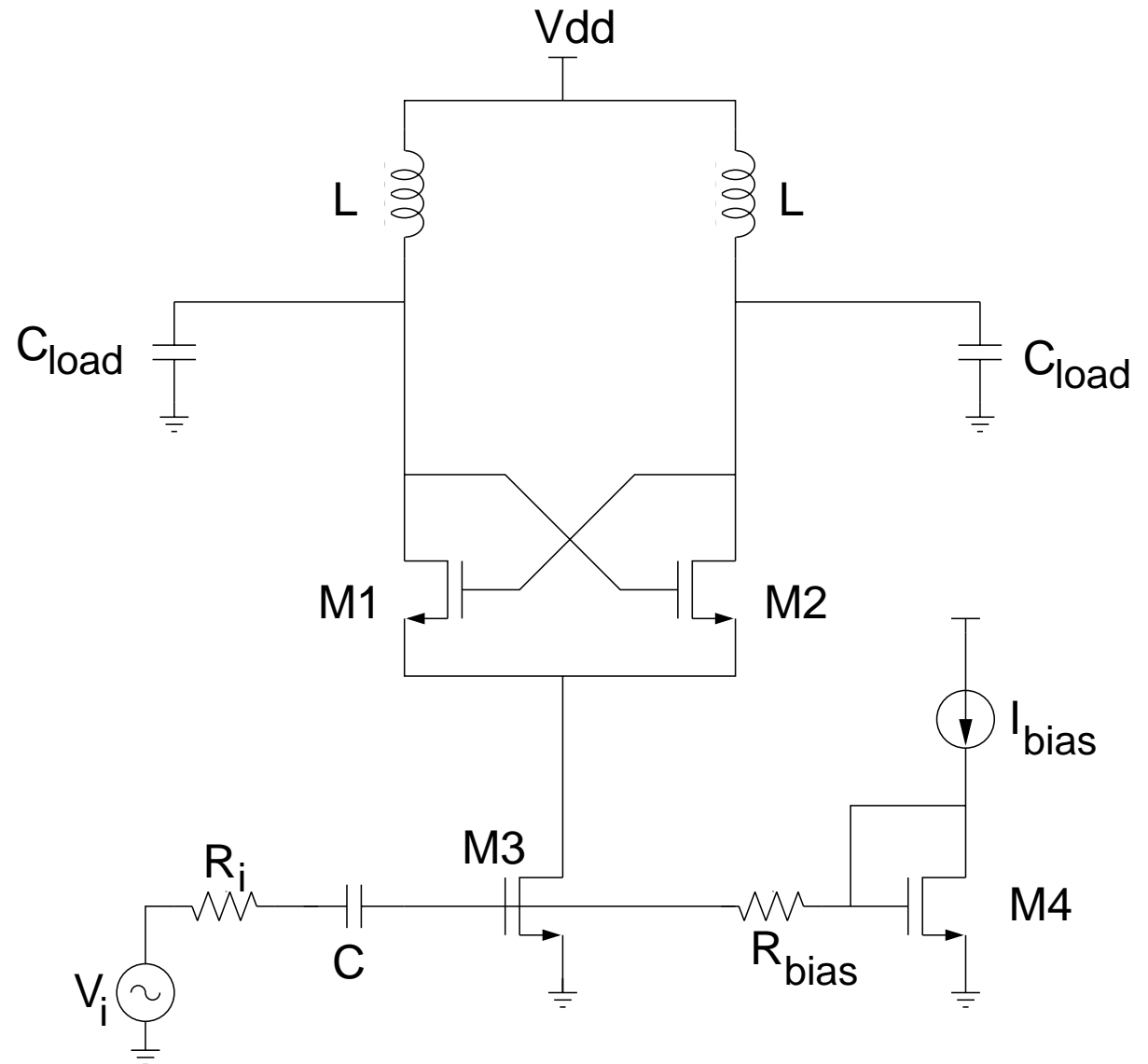
SIMULATIONS (SINGLE ENDED ILFD)

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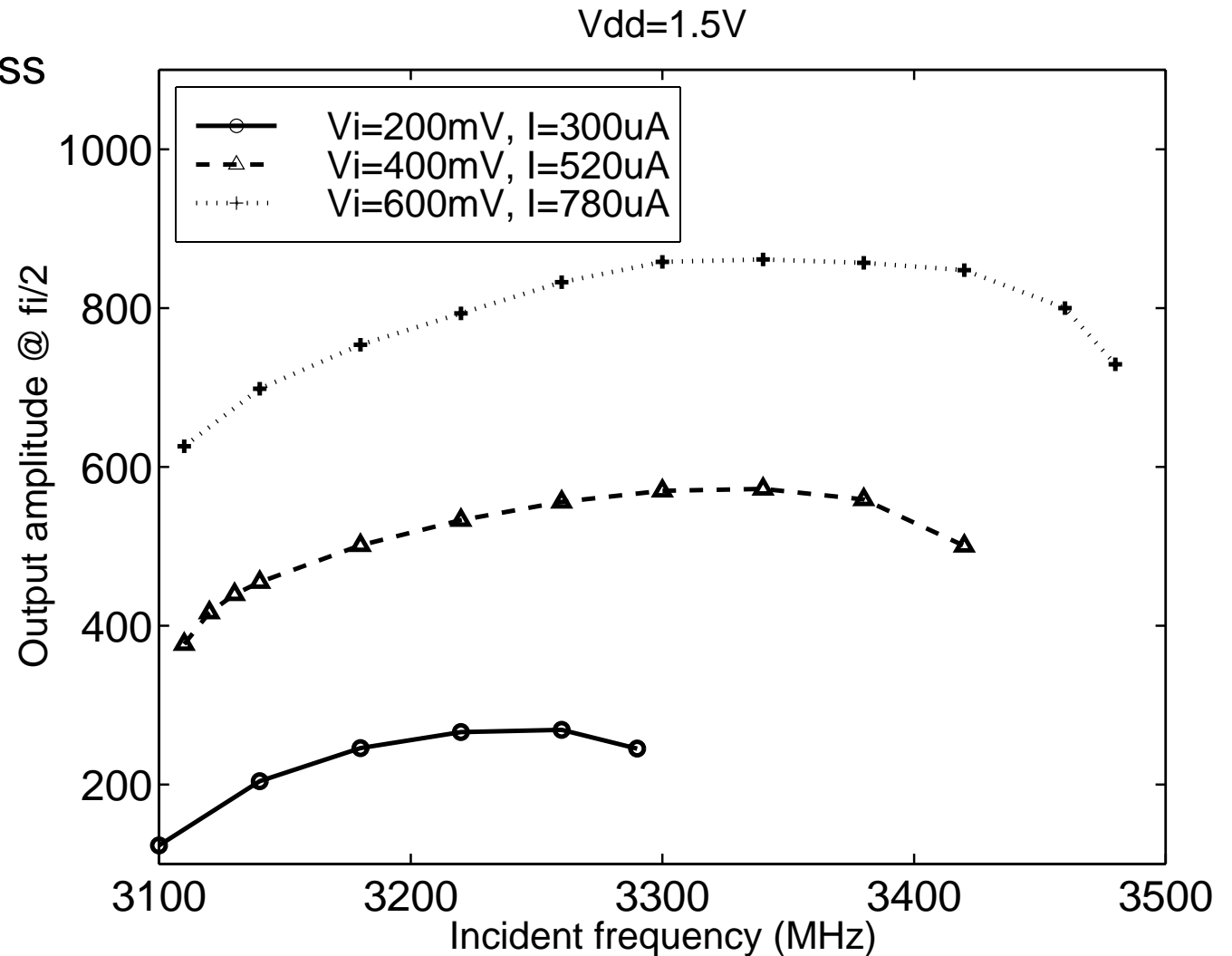
DIFFERENTIAL ILFD

- $0.5\mu\text{m}$ CMOS process
- $V_{\text{dd}}=1.5\text{V}$
- $I_{\text{bias}}=300\mu\text{A}$
- $f_o=1.6\text{GHz}$
- $f_i=3.2\text{GHz}$



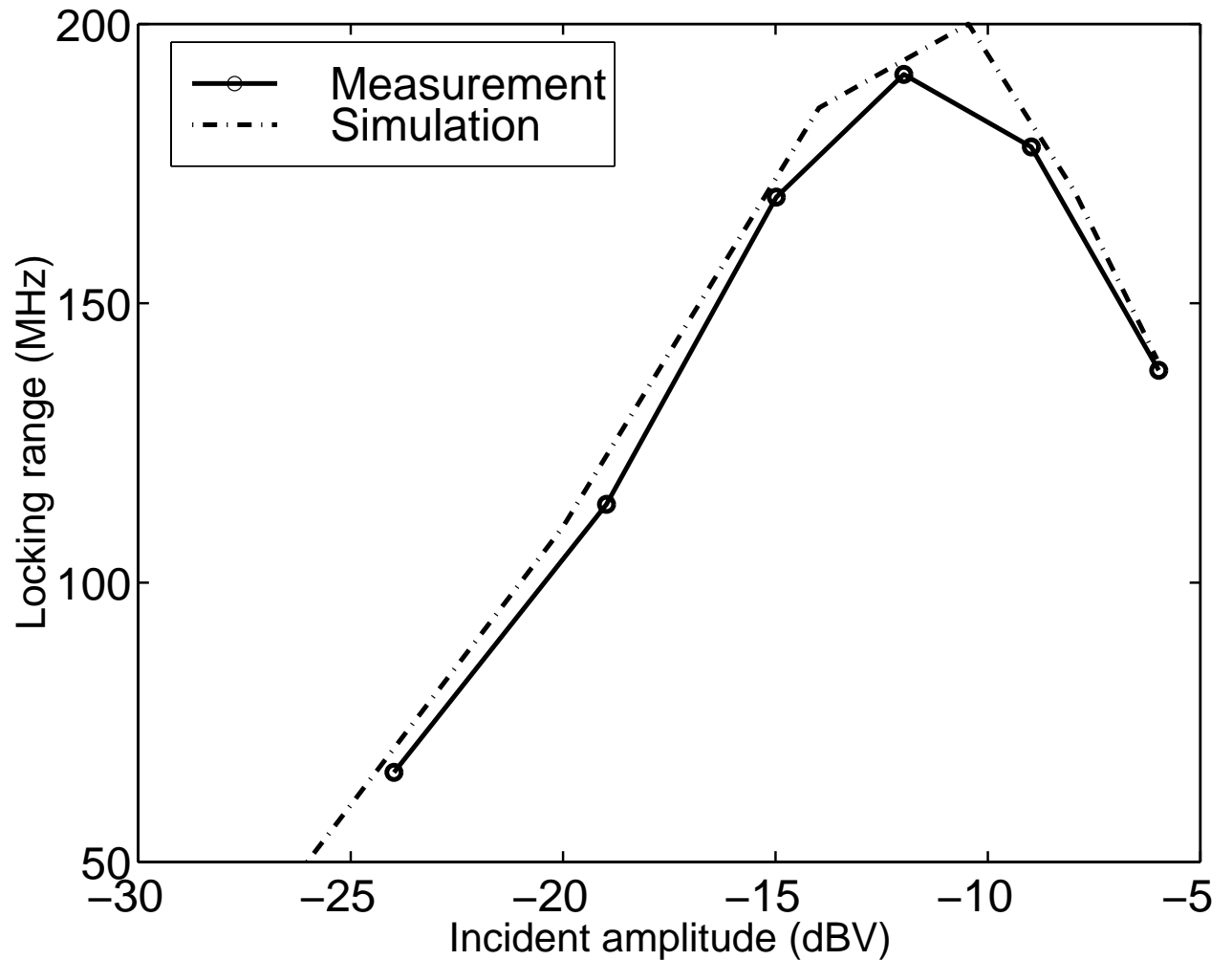
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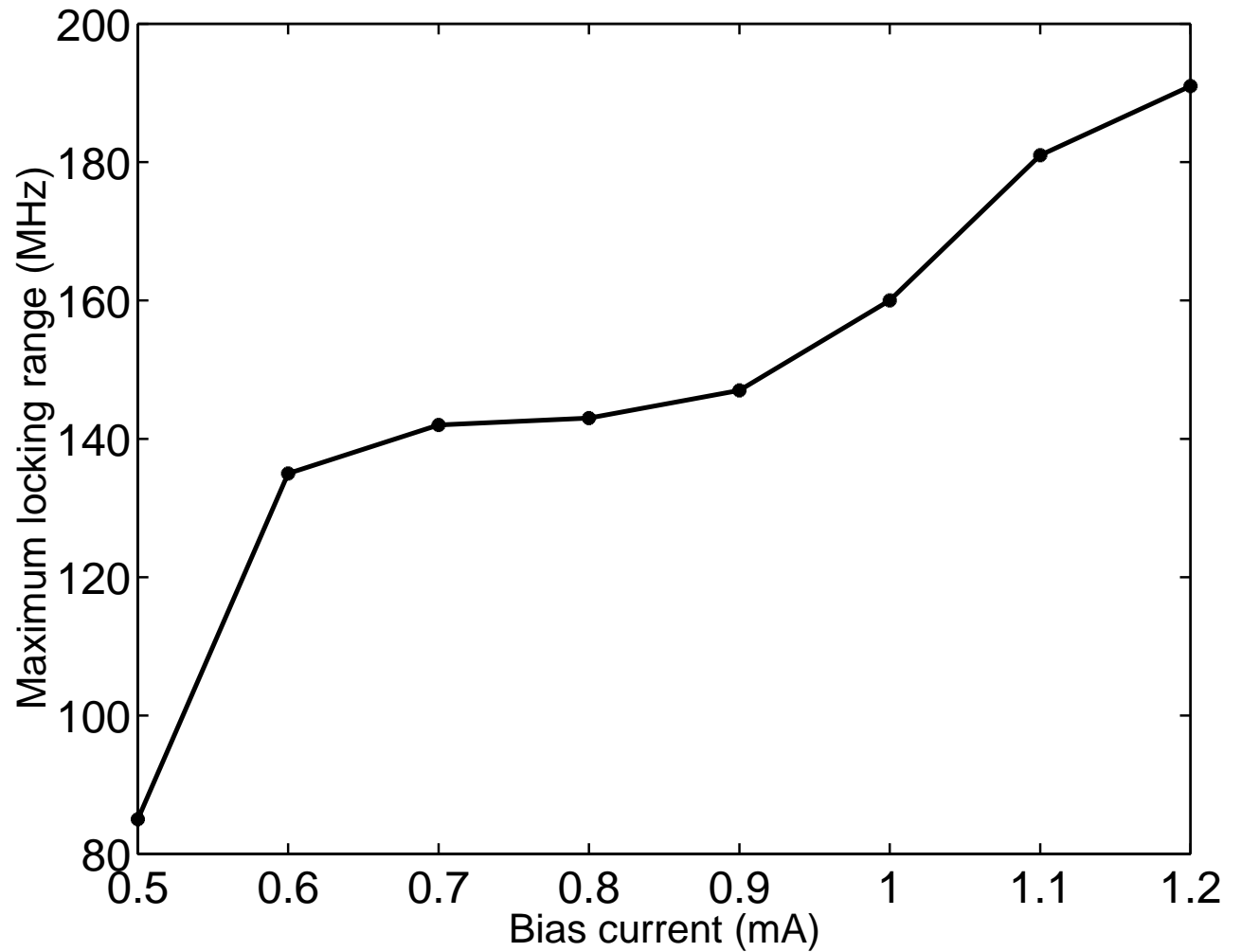
MEASUREMENTS (SINGLE ENDED ILFD)

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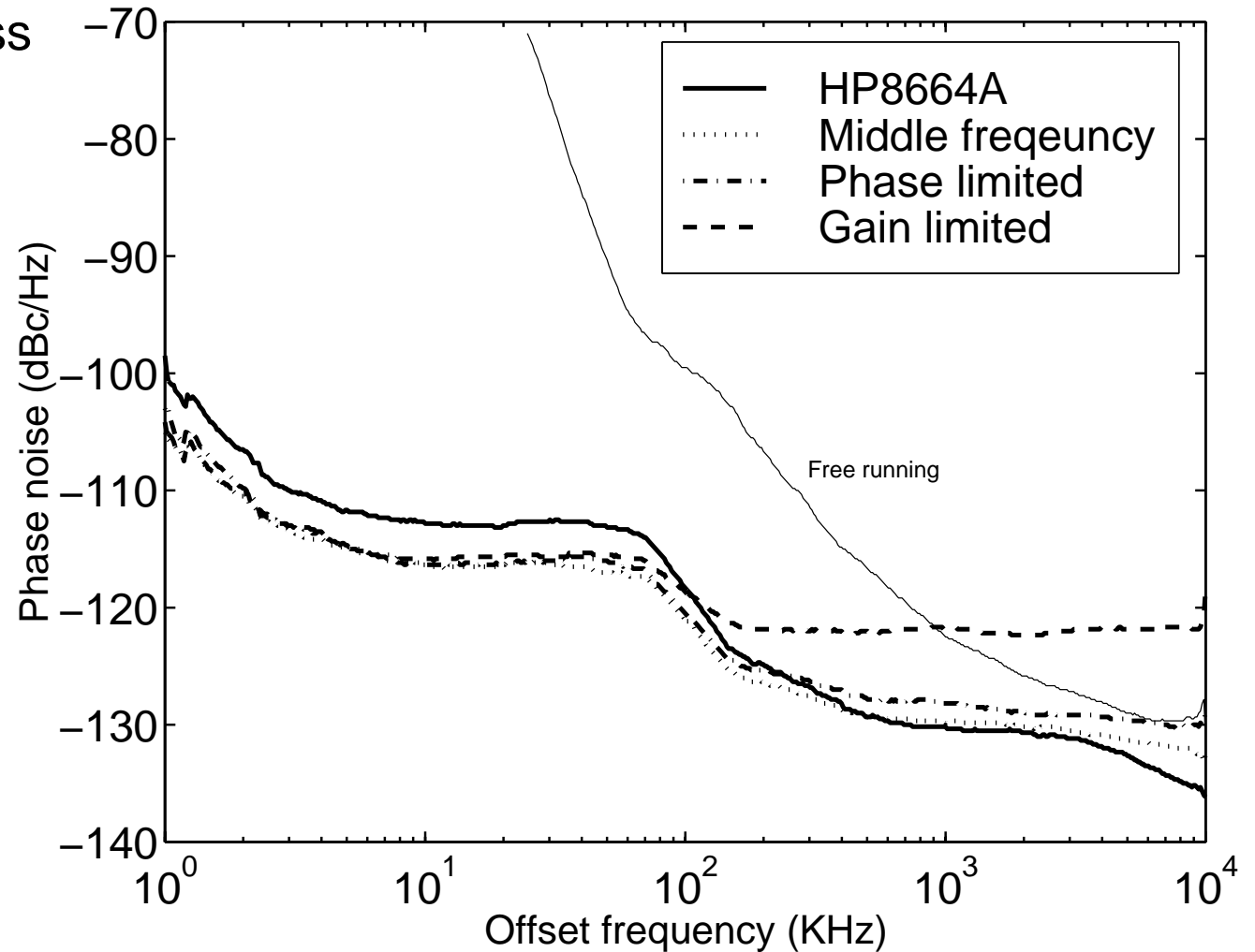
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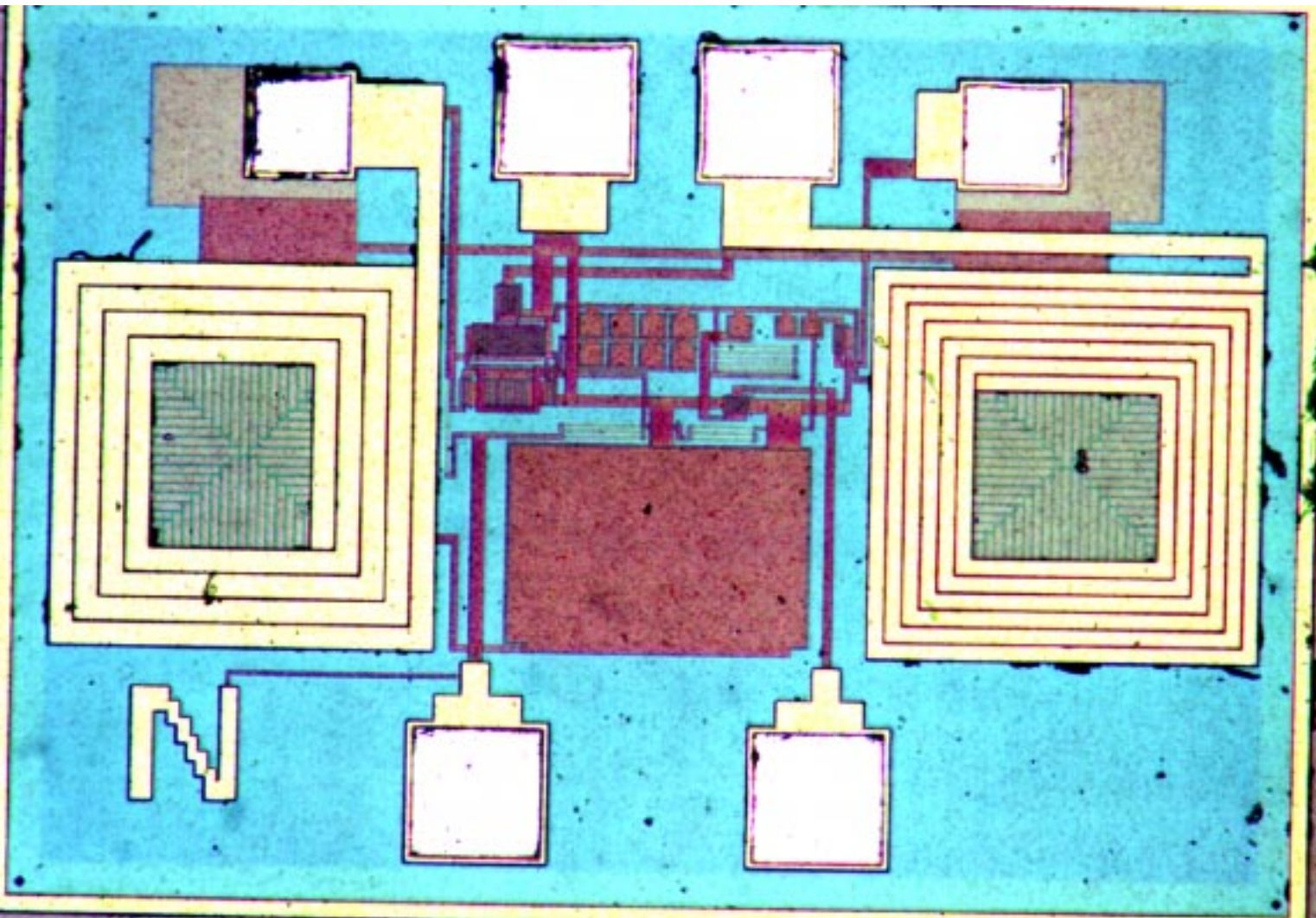


MEASUREMENTS (SINGLE ENDED ILFD)

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CHIP MICROGRAPH



PERFORMANCE SUMMARY

- $0.5\mu m$ CMOS process.

Divider	f (GHz)	Vdd(V)	I_{bias} (μA)	Power(mW)	Δf (MHz)
SiLFD (Measured)	1.8	2.5	600	1.5	135
			1200	3.0	191
DiLFD (Simulated)	3.5	1.5	300	0.45	190
			400	0.60	260
			780	1.17	370
SCL Flip-flop (Simulated)	1.8	2.0	1000	2.0	1800
	3.0	Failed			

CONCLUSION

- A new model for injection locked oscillators is developed which:
 - Predicts the locking range.
 - Describes two different mechanism through which injection locking fails.
- Superharmonic injection locked oscillators are designed as very high frequency and low power frequency dividers.
- Unlike conventional frequency dividers, the power consumption of an ILFD does not necessarily increase with frequency of operation.
- Using injection locking techniques, one can design frequency dividers at frequencies where conventional architectures fail.

ACKNOWLEDGMENT

Ali Hajimiri

Rockwell Semiconductor Systems

Dr. Christopher Hull

Frederic Stubbe

Pascal Tran